

## AO3703

### P-Channel Enhancement Mode Field Effect Transistor with Schottky Diode

#### General Description

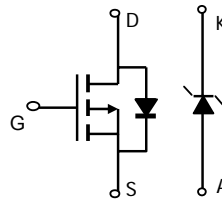
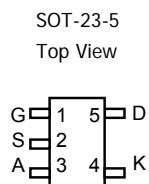
The AO3703 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. A Schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications. *Standard Product AO3703 is Pb-free (meets ROHS & Sony 259 specifications). AO3703L is a Green Product ordering option. AO3703 and AO3703L are electrically identical.*

#### Features

$V_{DS}$  (V) = -20V  
 $I_D$  = -2.7 A ( $V_{GS}$  = -10V)  
 $R_{DS(ON)}$  < 97m $\Omega$  ( $V_{GS}$  = -4.5V)  
 $R_{DS(ON)}$  < 130m $\Omega$  ( $V_{GS}$  = -2.5V)  
 $R_{DS(ON)}$  < 190m $\Omega$  ( $V_{GS}$  = -1.8V)

#### SCHOTTKY

$V_{DS}$  (V) = 20V,  $I_F$  = 1A,  $V_F$  < 0.5V@0.5A



#### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	$V_{DS}$	-20		V
Gate-Source Voltage	$V_{GS}$	$\pm 8$		V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ\text{C}$	-2.7	A
		$T_A=70^\circ\text{C}$	-2.1	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-10		
Schottky reverse voltage	$V_{KA}$		20	V
Continuous Forward Current <sup>A</sup>	$I_F$	$T_A=25^\circ\text{C}$	2	A
		$T_A=70^\circ\text{C}$	1	
Pulsed Forward Current <sup>B</sup>	$I_{FM}$		10	
Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	1.14	W
		$T_A=70^\circ\text{C}$	0.72	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	-55 to 150	$^\circ\text{C}$

Parameter: Thermal Characteristics MOSFET	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup> $t \leq 10\text{s}$	$R_{\theta JA}$	80.3	110	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup> Steady-State		117	150	
Maximum Junction-to-Lead <sup>C</sup> Steady-State	$R_{\theta JL}$	58.5	80	

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-20			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-16V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±8V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA	-0.3	-0.6	-1	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-5V	-10			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2.7A T <sub>J</sub> =125°C		76 111	97 135	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2A		101	130	mΩ
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-1A		134	190	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-2.7A	4	7		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.78	-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-2	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance			540		pF
C <sub>oss</sub>	Output Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-10V, f=1MHz		72		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			49		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		12		Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub>	Total Gate Charge			6.1		nC
Q <sub>gs</sub>	Gate Source Charge	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V, I <sub>D</sub> =-2.7A		0.6		nC
Q <sub>gd</sub>	Gate Drain Charge			1.6		nC
t <sub>D(on)</sub>	Turn-On Delay Time			10		ns
t <sub>r</sub>	Turn-On Rise Time	V <sub>GS</sub> =-4.5V, V <sub>DS</sub> =-10V, R <sub>L</sub> =2.8Ω,		12		ns
t <sub>D(off)</sub>	Turn-Off Delay Time	R <sub>GEN</sub> =3Ω		44		ns
t <sub>f</sub>	Turn-Off Fall Time			22		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-2.7A, dI/dt=100A/μs		21		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-2.7A, dI/dt=100A/μs		7.5		nC
<b>SCHOTTKY PARAMETERS</b>						
V <sub>F</sub>	Forward Voltage Drop	I <sub>F</sub> =0.5A		0.39	0.5	V
I <sub>rm</sub>	Maximum reverse leakage current	V <sub>R</sub> =16V			0.1	mA
		V <sub>R</sub> =16V, T <sub>J</sub> =125°C			20	
C <sub>T</sub>	Junction Capacitance	V <sub>R</sub> =10V		34		pF
t <sub>rr</sub>	Schottky Reverse Recovery Time	I <sub>F</sub> =1A, dI/dt=100A/μs		5.2	10	ns
Q <sub>rr</sub>	Schottky Reverse Recovery Charge	I <sub>F</sub> =1A, dI/dt=100A/μs		0.8		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating. Rev0: July 2006

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

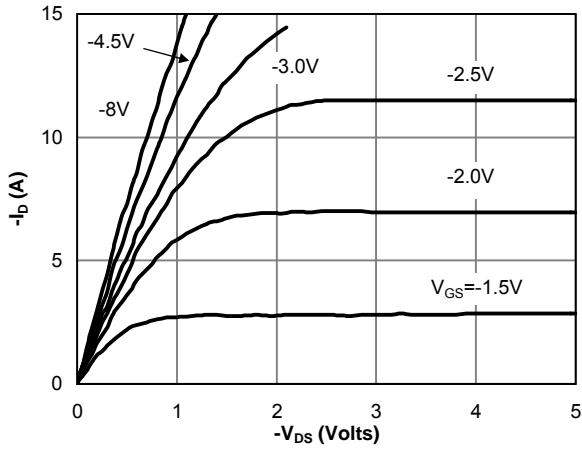


Fig 1: On-Region Characteristics

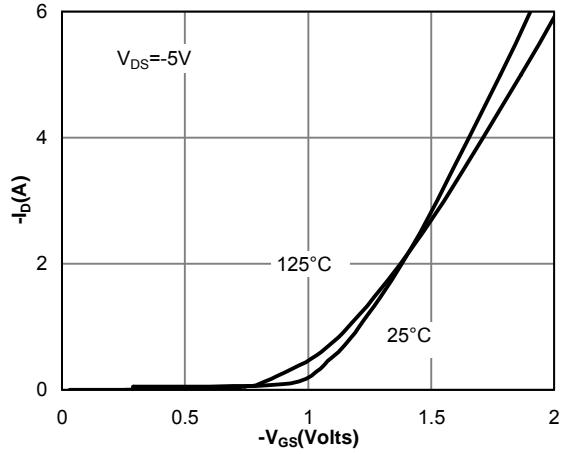


Figure 2: Transfer Characteristics

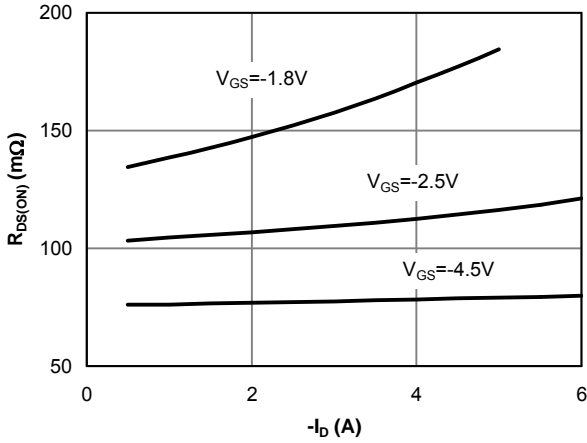


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

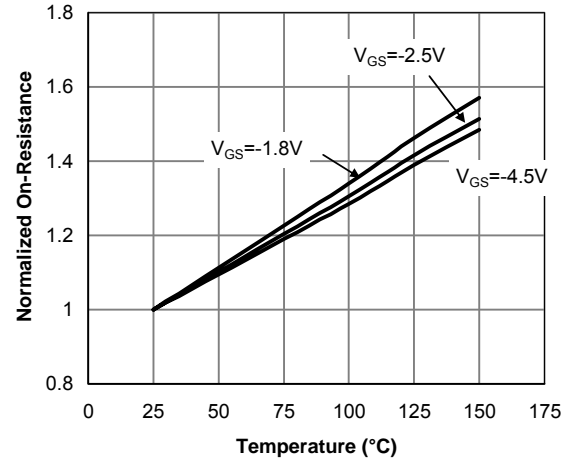


Figure 4: On-Resistance vs. Junction Temperature

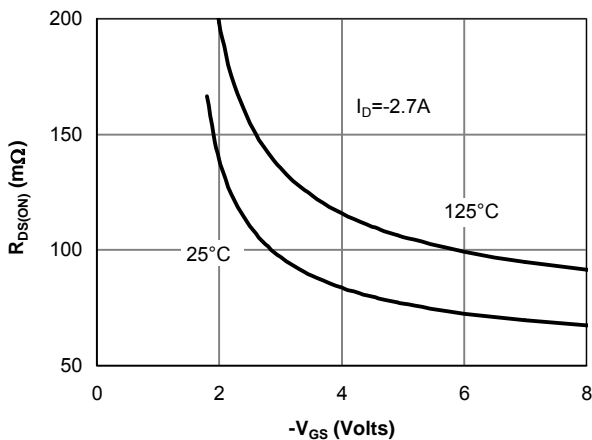


Figure 5: On-Resistance vs. Gate-Source Voltage

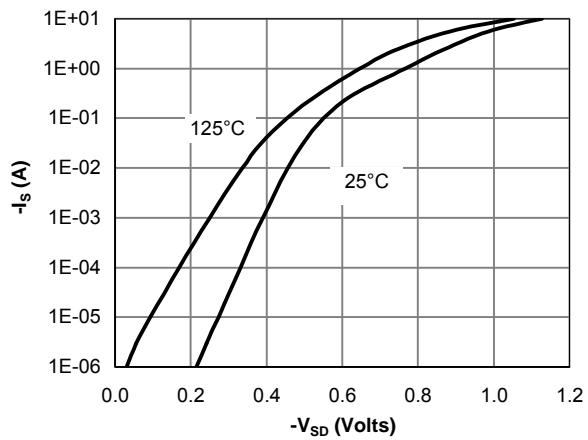


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

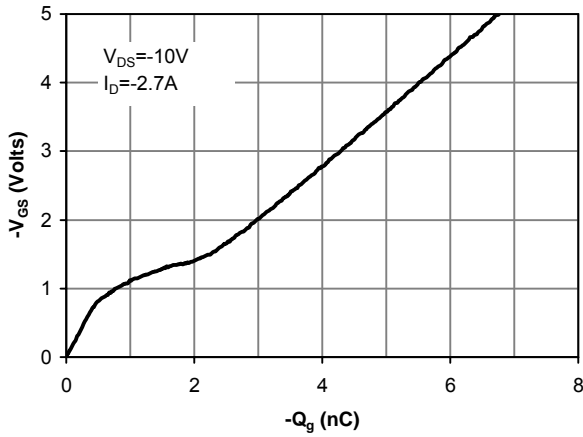


Figure 7: Gate-Charge Characteristics

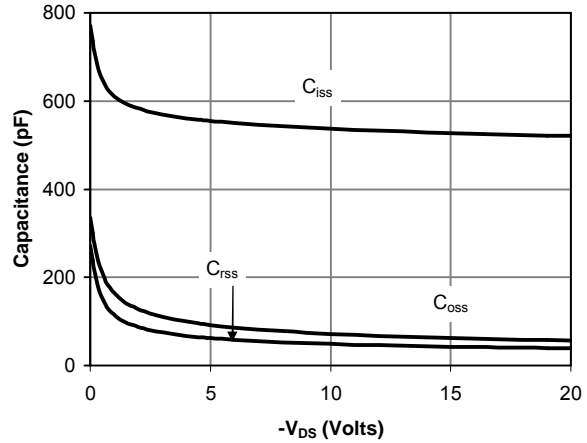


Figure 8: Capacitance Characteristics

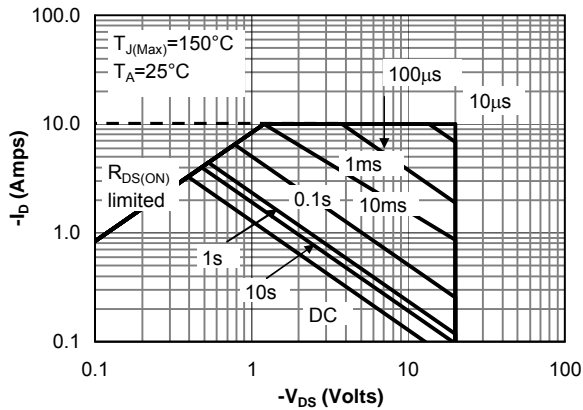


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

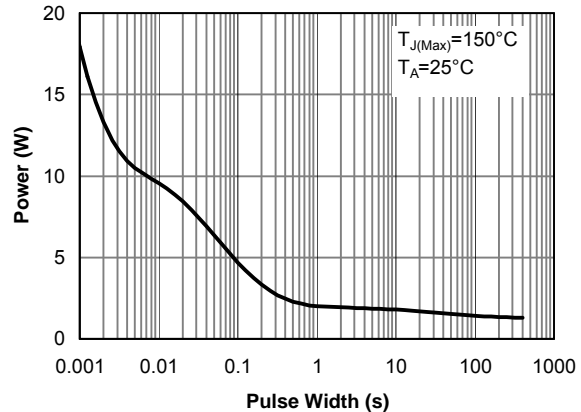


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

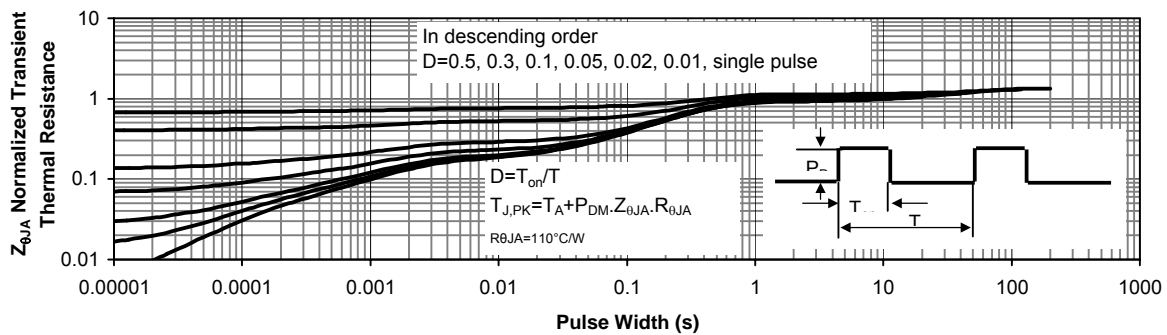


Figure 11: Normalized Maximum Transient Thermal Impedance